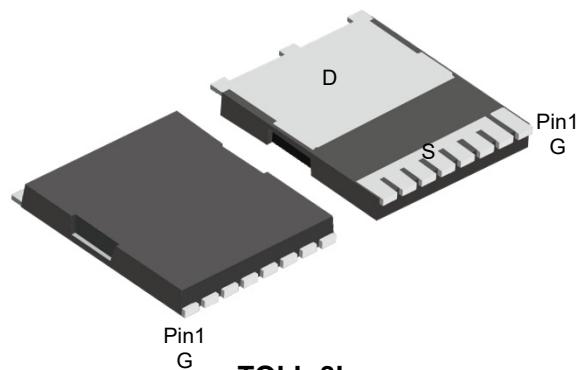


## Description

The PSMTL10R2H uses split gate trench technology to provide excellent  $R_{DS(ON)}$  low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
100	1.7@ $V_{GS} = 10V$	280



## Feature

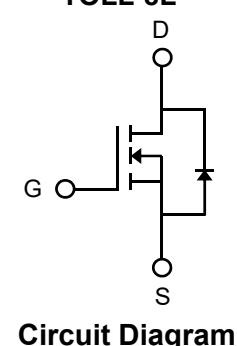
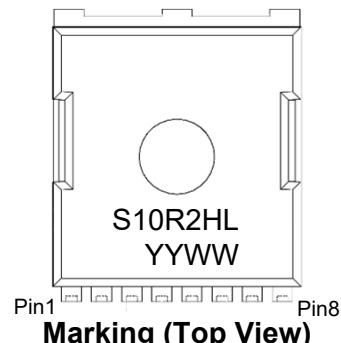
- Low  $R_{DS(ON)}$  - Ensures On-State Losses are Minimized
- Excellent  $Q_{gd} \times R_{DS(ON)}$  Product(FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% UIS (Avalanche) Rated
- Lead-Free Finish ; RoHS Compliant
- Halogen and Antimony Free. "Green" Device

## Applications

- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers

## Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous <sup>1)</sup>	$I_D$	280	A
$T_C=100^\circ C$		178	
Pulsed Drain Current <sup>2)</sup>	$I_{DM}$	1120	A
Total Power Dissipation <sup>3)</sup>	$P_D$	308.6	W
Avalanche Current <sup>4)</sup>	$I_{AS}$	119	A
Avalanche Energy <sup>4)</sup>	$E_{AS}$	2147	mJ
Thermal Resistance , Junction-case <sup>5)</sup>	$R_{\theta JC}$	0.4	°C/W
Thermal Resistance Junction-to-Ambient <sup>6)</sup>	$R_{\theta JA}$	28.9	°C/W
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	°C


**Circuit Diagram**

**Marking (Top View)**

## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	110	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100V, V_{GS} = 0V$	-	-	1.0	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.2	3.3	3.8	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 50A$	-	1.7	2.5	$m\Omega$
<b>Dynamic Characteristics<sup>7)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 50V, V_{GS} = 0V, f = 1.0MHz$	-	12400	-	pF
Output Capacitance	$C_{oss}$		-	1873	-	
Reverse Transfer Capacitance	$C_{rss}$		-	29	-	
<b>Switching Characteristics<sup>7)</sup></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 50V, V_{GS} = 10V, R_G = 10\Omega, I_D = 50A$	-	99.9	-	ns
Turn-on Rise Time	$t_r$		-	95.8	-	
Turn-Off Delay Time	$t_{d(off)}$		-	195.8	-	
Turn-Off Fall Time	$t_f$		-	88.6	-	
Total Gate Charge	$Q_g$	$V_{DS} = 50V, V_{GS} = 10V, I_D = 50A$	-	171.3	-	nC
Gate-Source Charge	$Q_{gs}$		-	65.2	-	
Gate-Drain Charge	$Q_{gd}$		-	37.6	-	
Gate Resistance	$R_g$	f=1MHz, Open Drain	-	2.5	-	$\Omega$
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 1A$	-	0.7	1.3	V

Notes:

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature( $T_{J\_Max}=150^{\circ}C$ ).
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. This single-pulse measurement was taken under the following condition [ $L=300\mu H, V_{GS}=10V, V_{DS}=100V$ ]while it's value is limited by  $T_{J\_Max}=150^{\circ}C$
5. Device mounted on infinite heatsink
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
7. Guaranteed by design, not subject to production

## Typical Characteristics

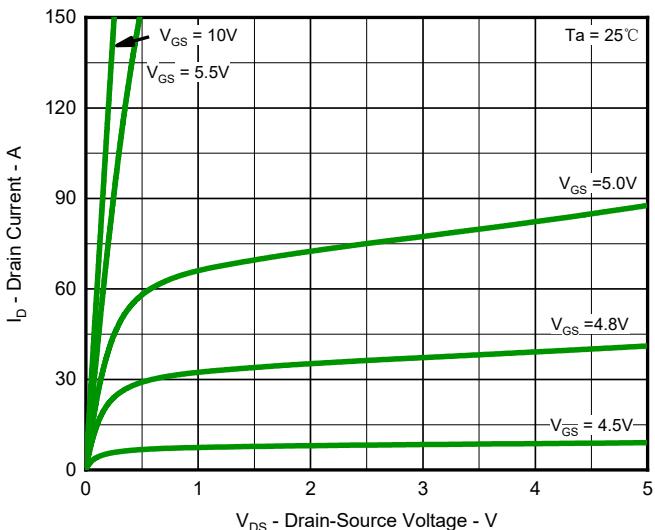


Fig.1 Output Characteristics

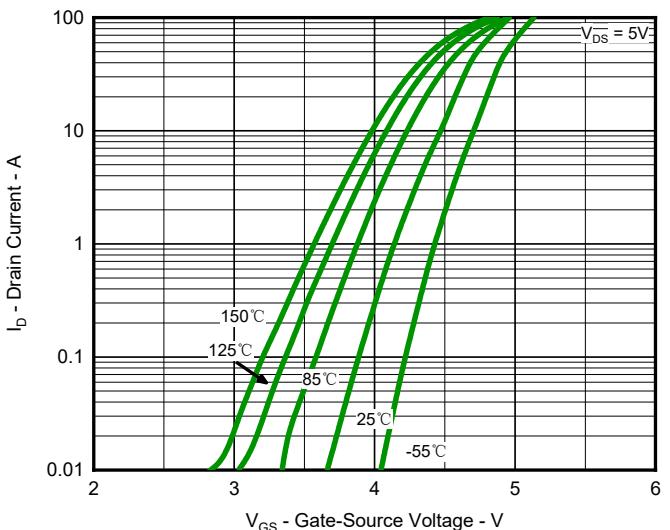


Fig.2 Typical Transfer Characteristic

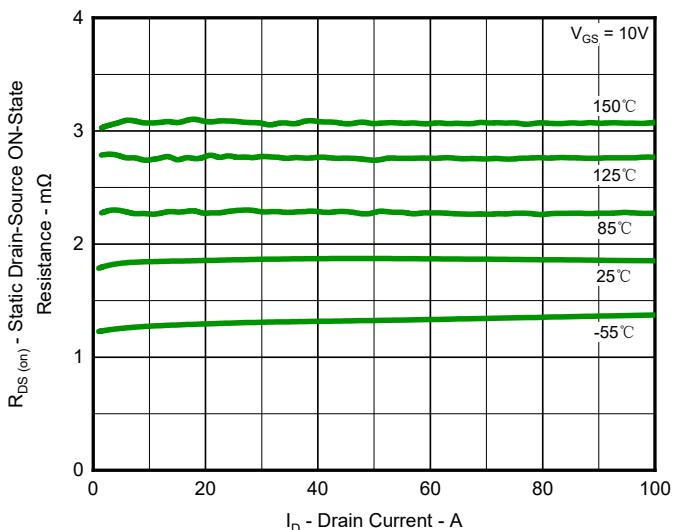


Fig.3 Typical On-Resistance vs. Drain Current and Temperature

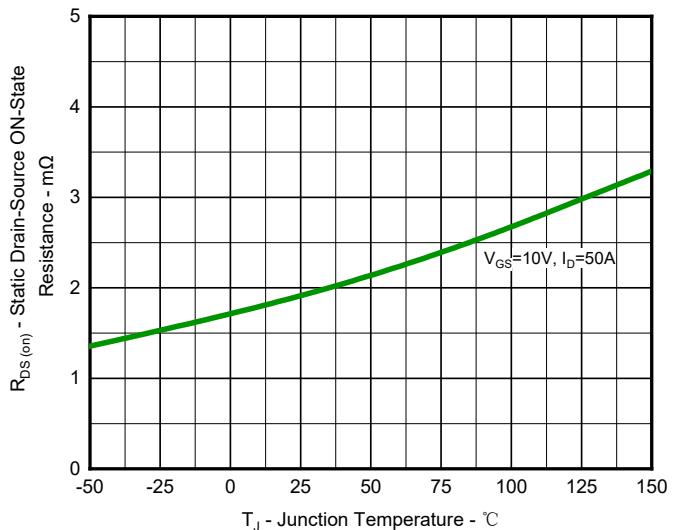


Fig.4 On-Resistance Variation with Temperature

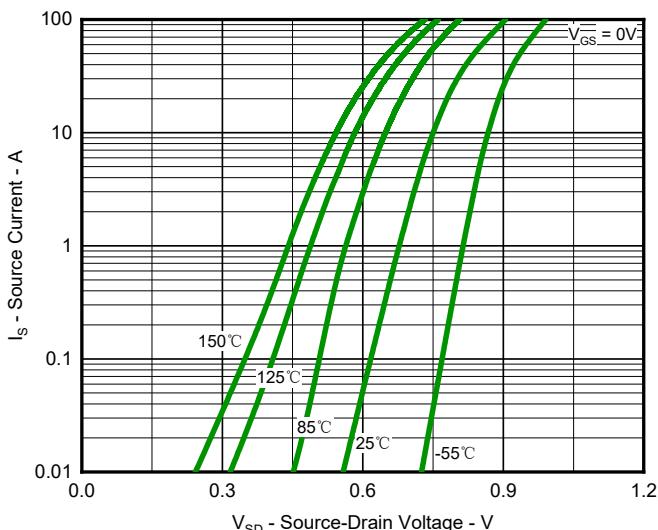


Fig.5 Diode Forward Voltage vs. Current

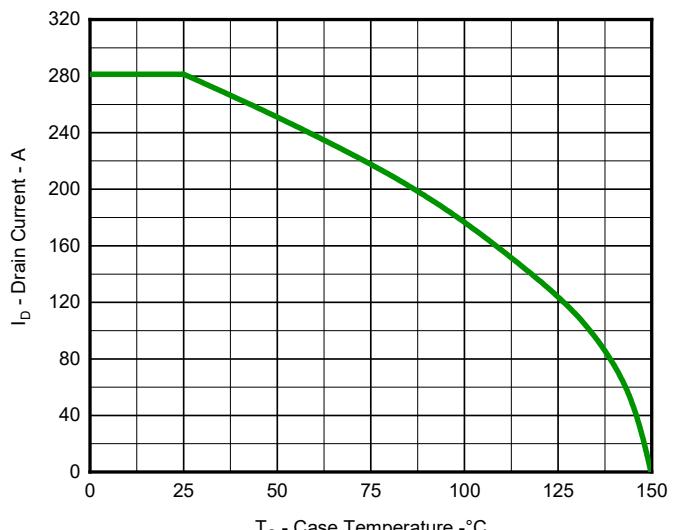
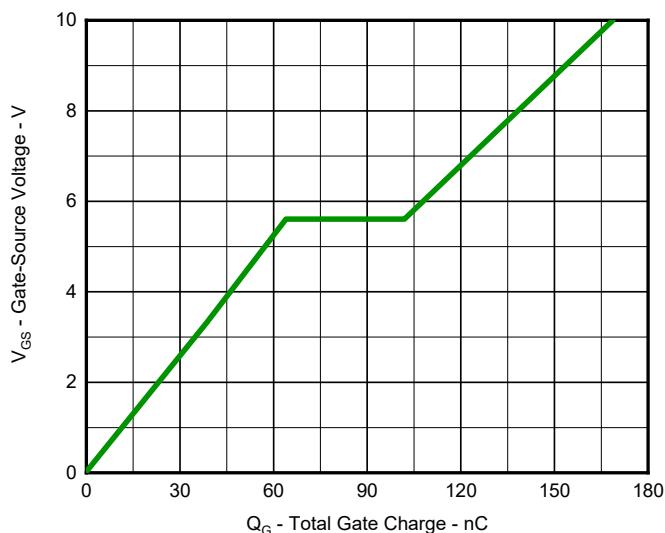


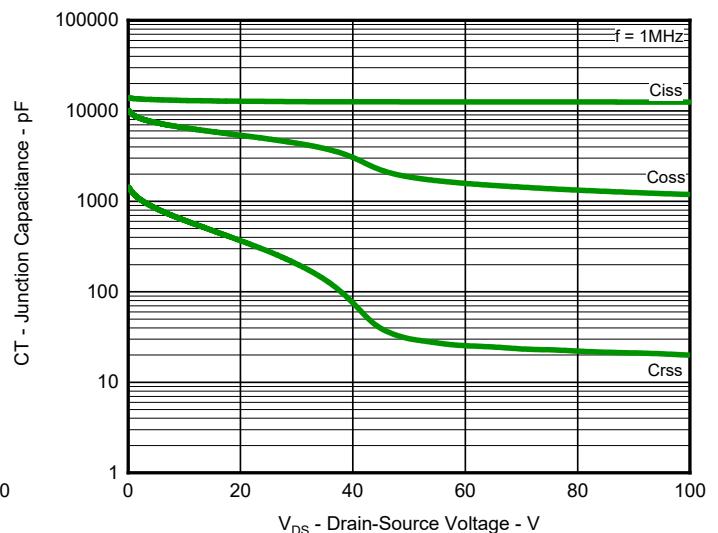
Fig.6 Maximum Drain Current vs. Case Temperature

# N-Channel MOSFET

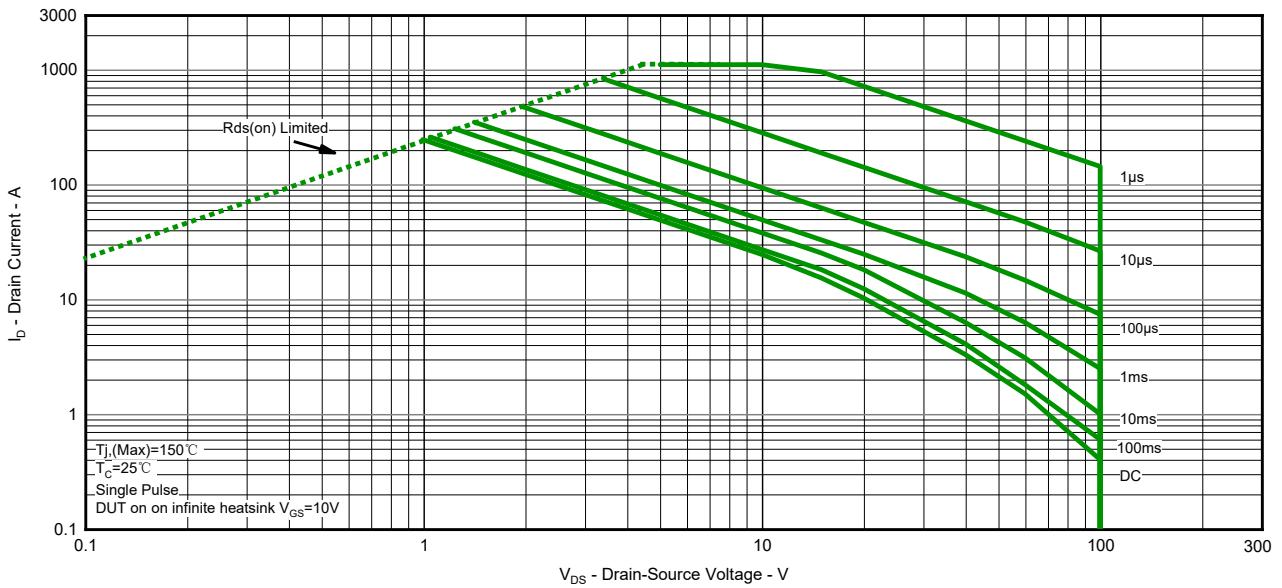
**PSMTL10R2H**



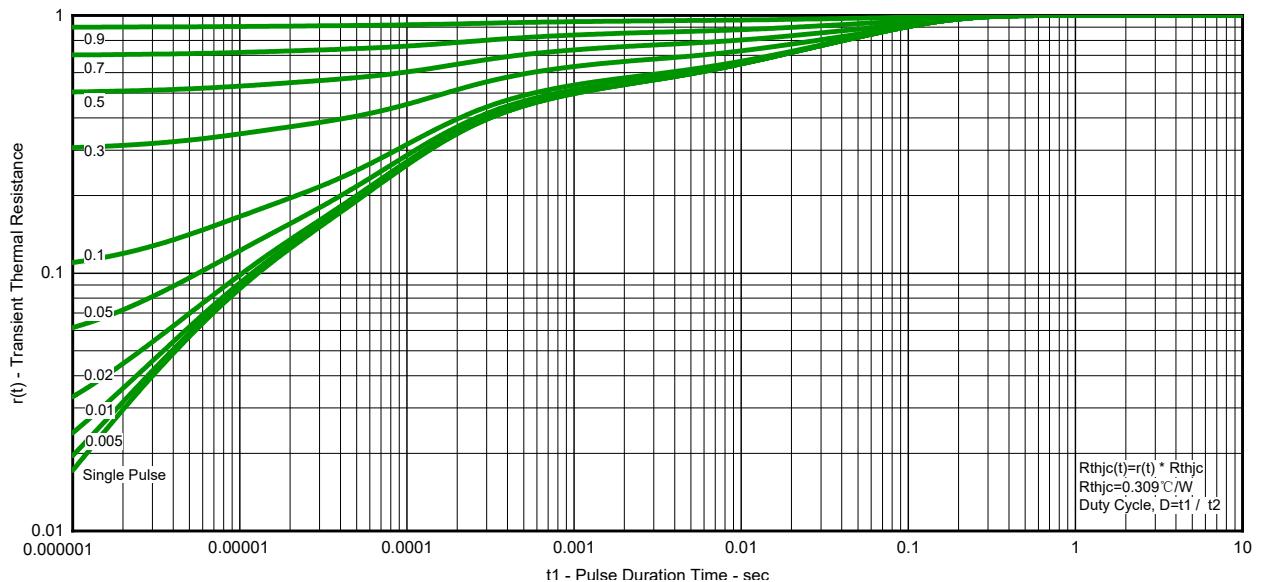
**Fig.7 Gate Charge Characteristics**



**Fig.8 Typical Junction Capacitance**

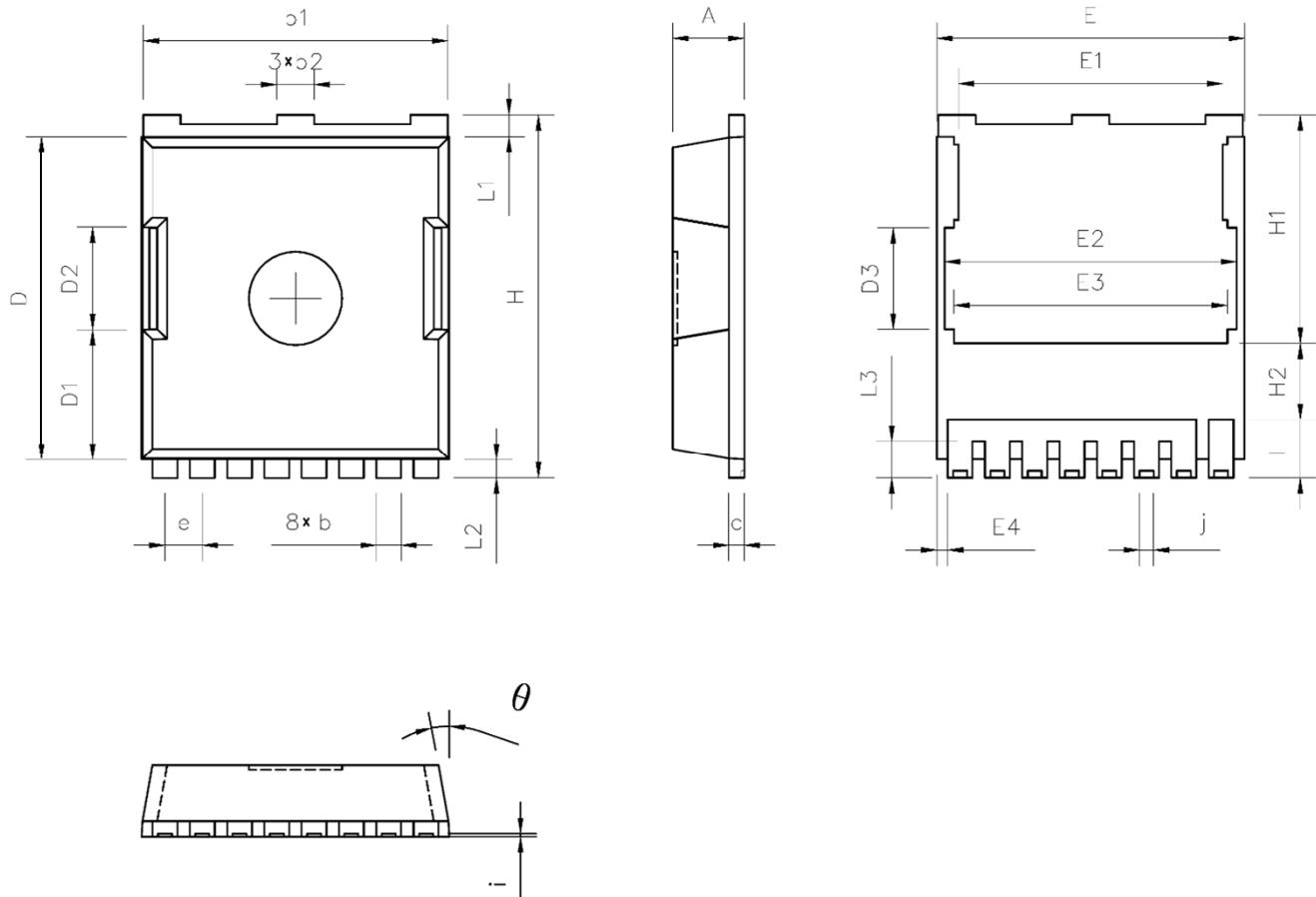


**Fig.9 Safe Operation Area**



**Fig.10 Transient Thermal Resistance**

## Product Dimension (TOLL-8L)

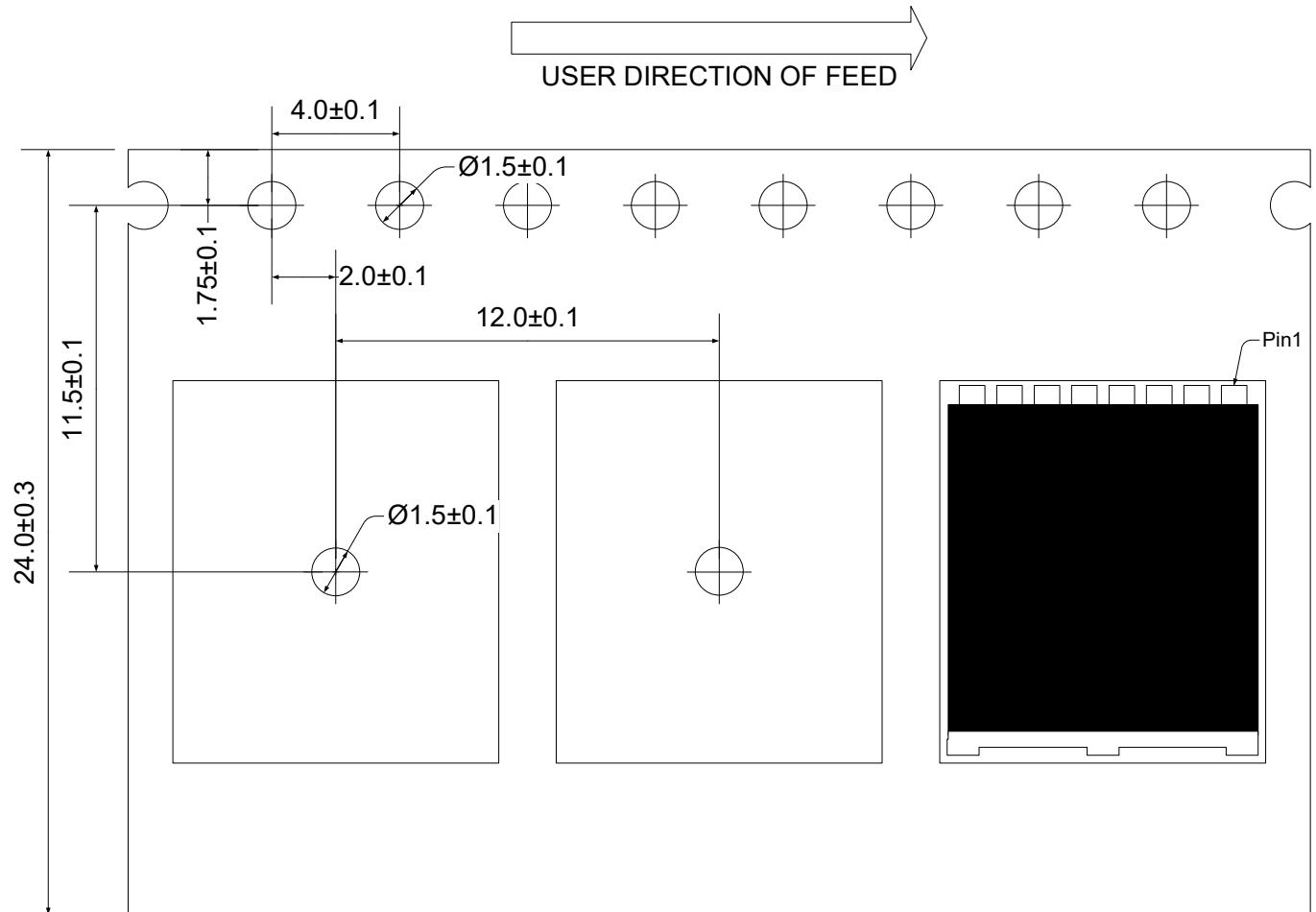


Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	2.20	2.40	0.087	0.094	E4	0.25	0.45	0.010	0.018
b	0.70	0.90	0.028	0.035	e	1.20 Basic		0.047 Basic	
b1	9.70	9.90	0.382	0.390	H	11.58	11.78	0.456	0.464
b2	1.20 Ref.		0.047 Ref.		H1	7.23	7.43	0.285	0.293
c	0.40	0.60	0.016	0.024	H2	2.45 Ref.		0.096	Ref.
D	10.28	10.48	0.405	0.413	i	0.10	-	0.004	-
D1	4.06	4.28	0.160	0.169	j	0.45 Ref.		0.018 Ref.	
D2	3.20	3.40	0.126	0.134	L	1.60	2.10	0.063	0.083
D3	3.16	3.36	0.124	0.132	L1	0.60	0.80	0.024	0.031
E	9.80	10.00	0.386	0.394	L2	0.50	0.70	0.020	0.028
E1	8.40	8.60	0.331	0.339	L3	1.05	1.30	0.041	0.051
E2	9.30	9.50	0.366	0.374	θ	10° Ref.		10° Ref.	
E3	8.80 Ref.		0.346 Ref.						

## Ordering Information

Device	Package	Reel	Shipping
PSMTL10R2H	TOLL-8L	13"	2000 / Tape & Reel

## Load With Information



Unit:mm

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